

HIGH VOLTAGE NPN SILICON TRANSISTOR

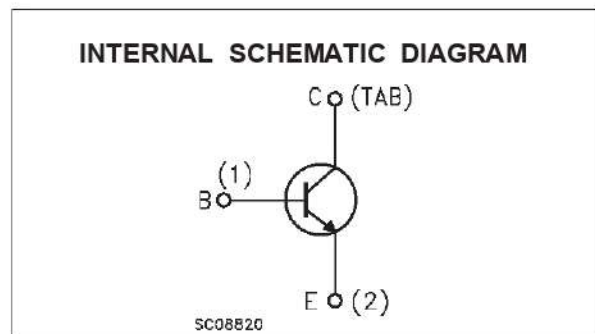
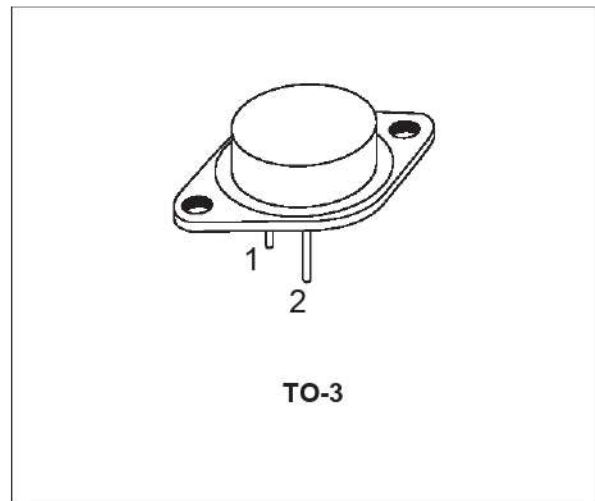
- STM PREFERRED SALESType
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- HIGH POWER TO-3 PACKAGE

APPLICATIONS:

- HORIZONTAL DEFLECTION FOR COLOUR TV
- SWITCHING REGULATORS

DESCRIPTION

The BUY69A is a silicon multiepitaxial mesa NPN transistor in Jedec TO-3 metal case. It is intended for horizontal deflection output stage of CTV receivers and high voltage, fast switching and industrial applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	1000	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	8	V
I_C	Collector Current	10	A
I_{CM}	Collector Peak Current ($t_p \leq 10$ ms)	15	A
I_B	Base Current	3	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ\text{C}$	100	W
T_{stg}	Storage Temperature	-65 to 200	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	200	$^\circ\text{C}$

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.75	$^{\circ}C/W$
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = 1000\text{ V}$			1	mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 8\text{ V}$			1	mA
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 100\text{ mA}$	1000			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 8\text{ A}$ $I_B = 2.5\text{ A}$			3.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 8\text{ A}$ $I_B = 2.5\text{ A}$			2.2	V
h_{FE}	DC Current Gain	$I_C = 2.5\text{ A}$ $V_{CE} = 10\text{ V}$	15			
f_T	Transition Frequency	$I_C = 0.5\text{ A}$ $V_{CE} = 10\text{ V}$		10		MHz
$I_{s/b}^{**}$	Second Breakdown Collector Current	$V_{CE} = 25\text{ V}$	4			A
t_{on}	Turn on Time	$I_C = 5\text{ A}$ $V_{CE} = 250\text{ V}$ $I_{B1} = 1\text{ A}$		0.2		μs
t_s t_s	Storage Time Fall Time	$I_C = 5\text{ A}$ $V_{CE} = 250\text{ V}$ $I_{B1} = -I_{B2} = 1\text{ A}$			1.7 0.3	μs μs
t_f	Fall Time	$I_C = 8\text{ A}$ $V_{CE} = 40\text{ V}$ $I_{B1} = -I_{B2} = 2.5\text{ A}$			1	μs

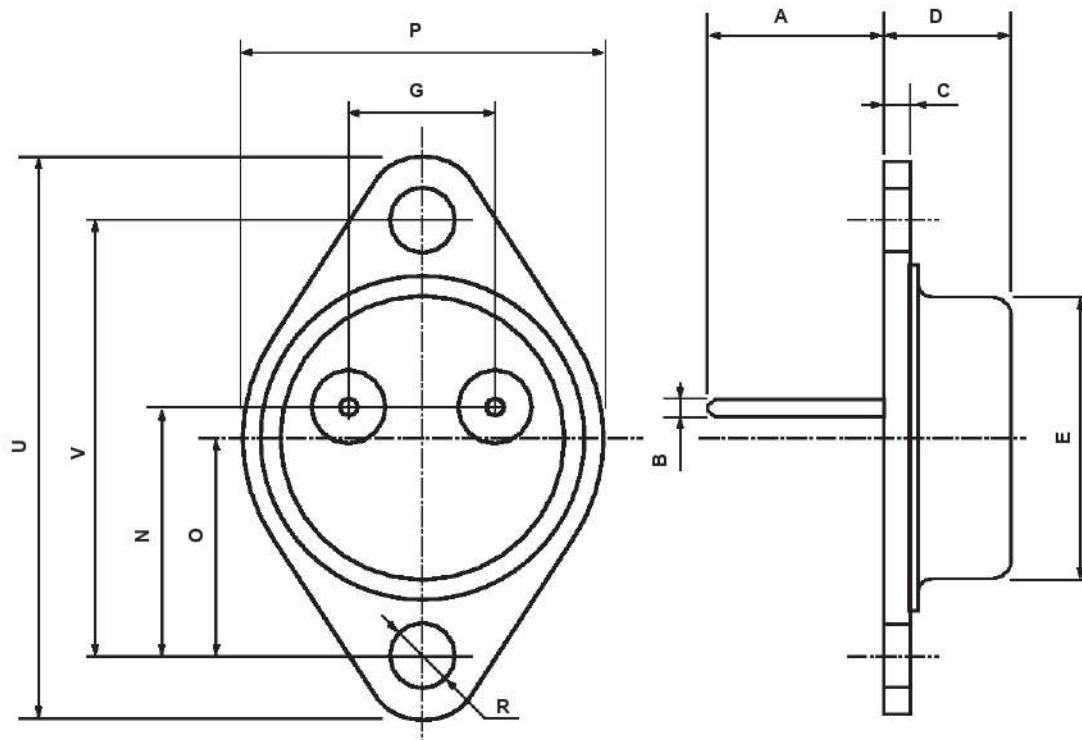
| | Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

| | | Pulsed: 1s, non repetitive pulse.

For characteristics curves see the BUW34/5/6 series.

TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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